BGU7052 SiGe:C Low Noise High Linearity Amplifier Rev. 2 — 21 February 2012

**Product data sheet** 

### 1. Product profile

### **1.1 General description**

The BGU7052 is a low noise high linearity amplifier for wireless infrastructure applications. The LNA has a high input and output return loss and is designed to operate between 1.5 GHz and 2.5 GHz. It is housed in a  $3 \times 3 \times 0.85$  mm<sup>3</sup> 10-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

### **1.2 Features and benefits**

- Low Noise Figure (NF) = 0.76 dB at 1900 MHz
- High linearity performance, IP3<sub>O</sub> = 35 dBm at 1900 MHz
- High input and output return loss
- Unconditionally stable
- 110 GHz transit frequency SiGe:C technology
- Supply voltage 3.3 V
- Small 10-terminal leadless package 3 × 3 × 0.85 mm<sup>3</sup>
- Moisture sensitivity level 1

### 1.3 Applications

- LNA for wireless infrastructure applications (1.5 GHz to 2.5 GHz)
- Low noise applications

### 1.4 Quick reference data

#### Table 1. Quick reference data

f = 1900 MHz;  $T_{amb}$  = 25 °C; input and output 50  $\Omega$ ; unless otherwise specified.

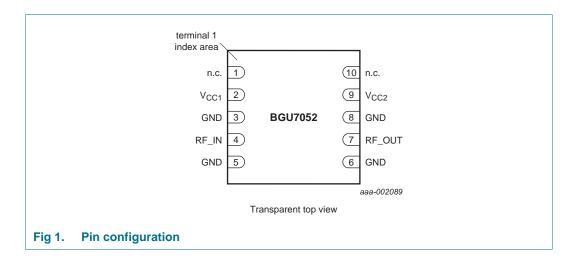
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CC</sub>	supply voltage		3.0	3.3	3.6	V
I <sub>CC</sub>	supply current		63	80	95	mA
G <sub>ass</sub>	associated gain		18.5	20	21.5	dB
NF	noise figure		-	0.76	0.95	dB
P <sub>L(1dB)</sub>	output power at 1 dB gain compression		13	14.5	-	dBm
IP3 <sub>0</sub>	output third-order intercept point		32	35	-	dBm



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### 2. Pinning information

### 2.1 Pinning



### 2.2 Pin description

#### Table 2. Pin description

Symbol	Pin	Description
n.c.	1, 10	not connected
GND	3, 5, 6, 8	ground
RF_IN	4	RF input
RF_OUT	7	RF output
V <sub>CC</sub>	2, 9	supply voltage

# 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BGU7052	HVSON10	plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body 3 x 3 x 0.85 mm	SOT650-1		

### SiGe:C Low Noise High Linearity Amplifier

# 4. Limiting values

Table 4.In accorda	Limiting values ance with the Absolute Ma	aximum Rating System (IEC 60134).			
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		0	5	V
P <sub>tot</sub>	total power dissipation		-	300	mW
$P_{i(RF)CW}$	continuous waveform RF input power	V <sub>CC</sub> = 3.3 V	-	20	dBm
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-40	+85	°C
$V_{ESD}$	electrostatic discharge voltage	Human Body Model (HBM); According JEDEC standard 22-A114E	-	4	kV
		Charged Device Model (CDM); According JEDEC standard 22-C101B	-	2	kV

# 5. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		20	K/W

### 6. Characteristics

#### Table 6.Characteristics

 $V_{CC} = 3.3 \text{ V}$ ;  $T_{amb} = 25 \text{ °C}$ ; input and output 50  $\Omega$ ; unless otherwise specified. All RF parameters are measured at the device RF in and RF output terminals.

SymbolParameterConditionsMinTypMaxI_CCsupply current638095Gassassociated gainf = 1750 MHz-21.5-f = 1900 MHz18.52021.5MFnoise figuref = 1750 MHz-19.7-PL(1dB)output power at 1 dB gain compressionf = 1750 MHz-0.76-F1900 MHz-15.5F2100 MHz-15.5PL(1dB)output power at 1 dB gain compressionf = 1750 MHz1314.5-F1930 MHz-14.5F1930 MHz-14.5F1930 MHz-14.5F1930 MHzF1930 MHz- <th></th> <th></th> <th></th> <th></th> <th></th> <th></th> <th></th> <th></th>								
$ \begin{array}{c} G_{ass} \\ G_{ass} \\ \end{array} \  \  \  \  \  \  \  \  \  \  \  \  \$	bol P	Parameter		Conditions	Min	Тур	Max	Unit
$ \begin{array}{cccc} f = 1900 \mbox{ MHz} & 18.5 & 20 & 21.5 \\ f = 1950 \mbox{ MHz} & - & 19.7 & - \\ f = 1950 \mbox{ MHz} & - & 0.76 & - \\ f = 1750 \mbox{ MHz} & - & 0.76 & 0.95 \\ f = 1900 \mbox{ MHz} & - & 0.79 & - \\ f = 1950 \mbox{ MHz} & - & 0.79 & - \\ \end{array} $	รเ	supply current			63	80	95	mA
$ \begin{array}{cccc} f = 1950 \mbox{ MHz} & - & 19.7 & - \\ \mbox{NF} & noise figure & f = 1750 \mbox{ MHz} & - & 0.76 & - \\ \hline f = 1900 \mbox{ MHz} & - & 0.76 & 0.95 \\ \hline f = 1950 \mbox{ MHz} & - & 0.79 & - \\ \mbox{P}_{L(1dB)} & output power at 1 \mbox{ dB gain compression} & \hline f = 1750 \mbox{ MHz} & - & 15.5 & - \\ \hline f = 1900 \mbox{ MHz} & - & 15.5 & - \\ \hline f = 1900 \mbox{ MHz} & 13 & 14.5 & - \\ \hline f = 1950 \mbox{ MHz} & - & 14.5 & - \\ \end{array} $	a	associated gain		f = 1750 MHz	-	21.5	-	dB
$ \begin{array}{cccc} \text{NF} & \text{noise figure} & \begin{array}{cccc} f = 1750 \ \text{MHz} & - & 0.76 & - \\ f = 1900 \ \text{MHz} & - & 0.76 & 0.95 \\ \hline f = 1950 \ \text{MHz} & - & 0.79 & - \\ \end{array} \\ \begin{array}{cccc} P_{L(1dB)} & \text{output power at 1 dB gain compression} & \begin{array}{ccccc} f = 1750 \ \text{MHz} & - & 15.5 & - \\ \hline f = 1900 \ \text{MHz} & - & 15.5 & - \\ \hline f = 1900 \ \text{MHz} & 13 & 14.5 & - \\ \hline f = 1950 \ \text{MHz} & - & 14.5 & - \\ \end{array} $		-	f = 1900 MHz	18.5	20	21.5	dB	
$ \begin{array}{cccc} f = 1900 \mbox{ MHz} & - & 0.76 & 0.95 \\ f = 1950 \mbox{ MHz} & - & 0.79 & - \\ \hline P_{L(1dB)} & \mbox{output power at 1 dB gain compression} & f = 1750 \mbox{ MHz} & - & 15.5 & - \\ \hline f = 1900 \mbox{ MHz} & 13 & 14.5 & - \\ \hline f = 1950 \mbox{ MHz} & - & 14.5 & - \\ \hline \end{array} $				f = 1950 MHz	-	19.7	-	dB
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$ \begin{array}{ccc} P_{L(1dB)} & \mbox{output power at 1 dB gain compression} & f = 1750 \mbox{ MHz} & - & 15.5 & - \\ \hline f = 1900 \mbox{ MHz} & 13 & 14.5 & - \\ \hline f = 1950 \mbox{ MHz} & - & 14.5 & - \\ \end{array} $			f = 1900 MHz	-	0.76	0.95	dB	
$f = 1900 \text{ MHz} \qquad 13 \qquad 14.5  -$ $f = 1950 \text{ MHz} \qquad - \qquad 14.5  -$				f = 1950 MHz	-	0.79	-	dB
f = 1950 MHz - 14.5 -	3) OI	output power at 1 d	B gain compression	f = 1750 MHz	-	15.5	-	dBm
			f = 1900 MHz	13	14.5	-	dBm	
$IP3_O$ output third-order intercept point $f = 1750 \text{ MHz}$ - $36.8$ -				f = 1950 MHz	-	14.5	-	dBm
	0	output third-order ir	ntercept point	f = 1750 MHz	-	36.8	-	dBm
f = 1900 MHz 32 35.3 -				f = 1900 MHz	32	35.3	-	dBm
f = 1950 MHz - 35.1 -				f = 1950 MHz	-	35.1	-	dBm

BGU7052

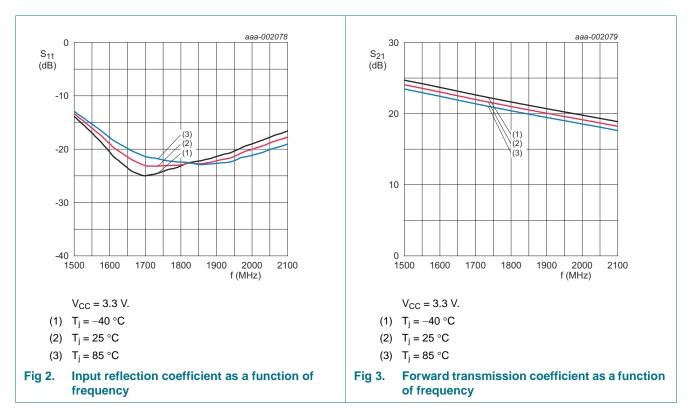
#### SiGe:C Low Noise High Linearity Amplifier

#### Table 6. Characteristics ...continued

 $V_{CC}$  = 3.3 V;  $T_{amb}$  = 25 °C; input and output 50  $\Omega$ ; unless otherwise specified. All RF parameters are measured at the device RF in and RF output terminals.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
RL <sub>in</sub>	input return loss	f = 1750 MHz	-	23	-	dB
		f = 1900 MHz	-	23	-	dB
		f = 1950 MHz	-	22	-	dB
RL <sub>out</sub>	output return loss	f = 1750 MHz	-	22	-	dB
		f = 1900 MHz	-	22	-	dB
		f = 1950 MHz	-	21	-	dB
ISL	isolation	f = 1750 MHz	-	28.5	-	dB
		f = 1900 MHz	-	27.5	-	dB
		f = 1950 MHz	-	27	-	dB
K	Rollett stability factor	$0 \; GHz \leq f \leq 25 \; GHz$	1	-	-	

### 6.1 Performance curves

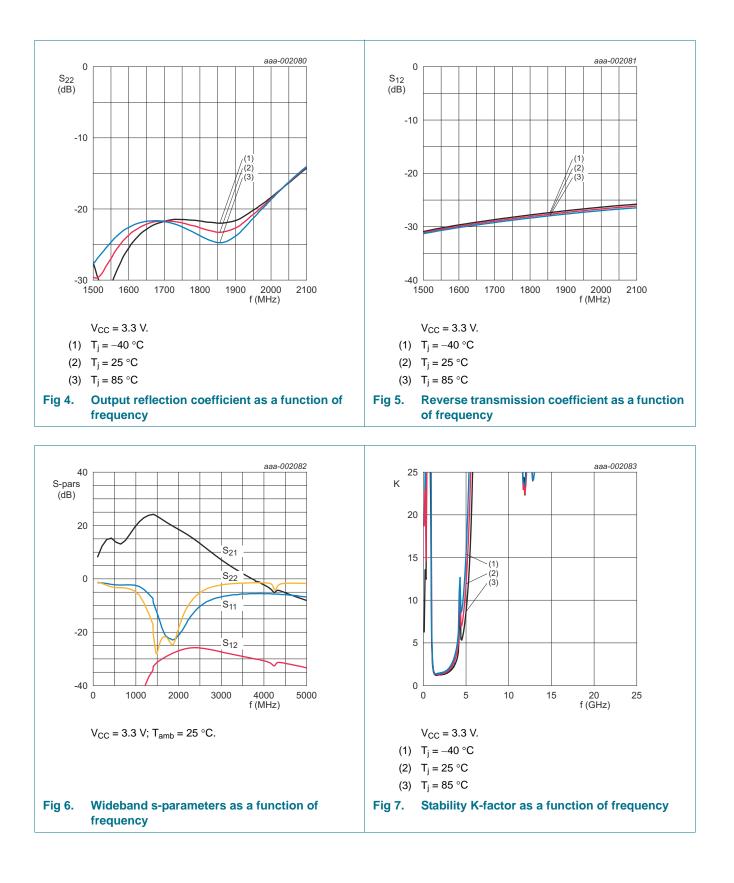


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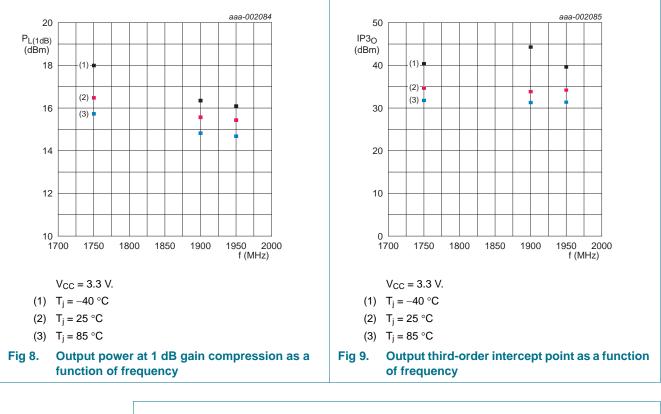


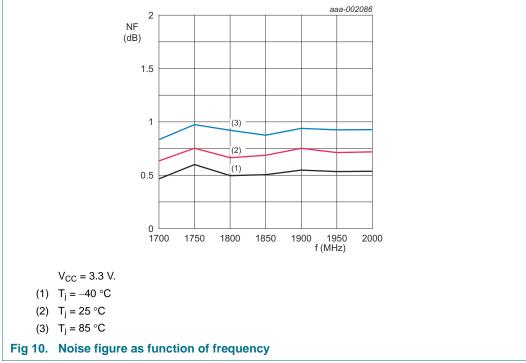
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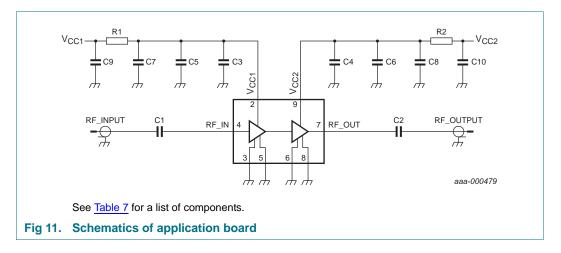


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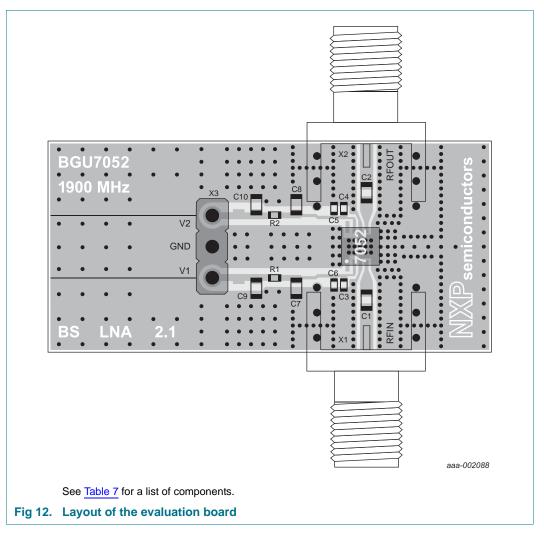
### 7. Application information

<u>Figure 11</u> shows the typical application circuit for the BGU7052. The device is internally matched to 50  $\Omega$ , and therefore does not need any external matching. The value of the input and output DC blocking C1 and C2 are recommended to be 1 nF. DC decoupling capacitors C3 and C4 should be located as close as possible to the BGU7052.

In case different system blocks are supplied via the same voltage rail, it is recommended to use a bias choke in the bias line on the positions of R1 and R2. The value of this choke is depending on the frequency that needs to be dececoupled.



### SiGe:C Low Noise High Linearity Amplifier



# Table 7.List of componentsSee Figure 11 for schematics.

-					
Component	Description		Value	Size	Function
C1, C2	capacitor	<u>[1]</u>	1 nF	0402	DC block
C3, C4	capacitor	<u>[1]</u>	100 pF	0402	bias decoupling
C5, C6	capacitor	<u>[1]</u>	100 nF	0402	bias decoupling
C7, C8, C9, C10	capacitor	[2]	100 nF	0603	optional
R1, R2	resistor		0 Ω	0402	

[1] Murata GRM155 or capacitor of same quality.

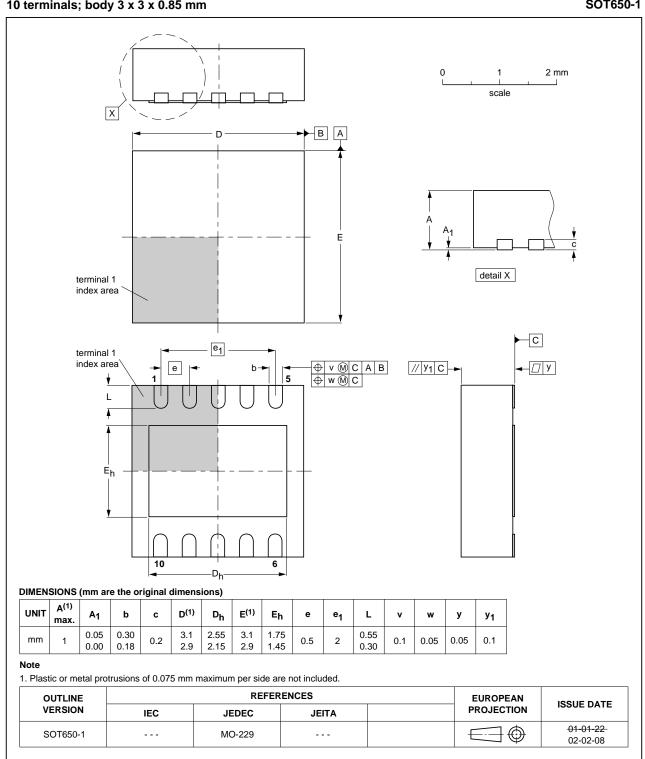
[2] Murata GRM188 or capacitor of same quality.

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#### **Package outline** 8.



### HVSON10: plastic thermal enhanced very thin small outline package; no leads; 10 terminals; body 3 x 3 x 0.85 mm

SOT650-1

Fig 13. Package outline SOT650-1 (HVSON10)

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**Product data sheet** 

9 of 13

SiGe:C Low Noise High Linearity Amplifier

# 9. Abbreviations

AcronymDescriptionACAlternating CurrentESDElectroStatic DischargeHBMHuman Body ModelLNALow Noise AmplifierPDAPersonal Digital Assistant	Table 8.	Abbreviations
ESDElectroStatic DischargeHBMHuman Body ModelLNALow Noise AmplifierPDAPersonal Digital Assistant	Acronym	Description
HBM     Human Body Model       LNA     Low Noise Amplifier       PDA     Personal Digital Assistant	AC	Alternating Current
LNALow Noise AmplifierPDAPersonal Digital Assistant	ESD	ElectroStatic Discharge
PDA Personal Digital Assistant	HBM	Human Body Model
	LNA	Low Noise Amplifier
	PDA	Personal Digital Assistant
RF Radio Frequency	RF	Radio Frequency
SiGe:C Silicon Germanium Carbon	SiGe:C	Silicon Germanium Carbon

# 10. Revision history

Table 9. Revisio	n history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BGU7052 v.2	20120221	Product data sheet	-	BGU7052 v.1
Modifications:	• <u>Table 6</u> : upda	ted		
BGU7052 v.1	20120214	Product data sheet	-	-

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Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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### SiGe:C Low Noise High Linearity Amplifier

### 13. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 2
2.1	Pinning 2
2.2	Pin description 2
3	Ordering information 2
4	Limiting values 3
5	Thermal characteristics 3
6	Characteristics
6.1	Performance curves 4
7	Application information
8	Package outline 9
9	Abbreviations 10
10	Revision history 10
11	Legal information 11
11.1	Data sheet status 11
11.2	Definitions 11
11.3	Disclaimers 11
11.4	Trademarks 12
12	Contact information 12
13	Contents 13

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